

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) An electret condenser, comprising:

a first electrode which is a fixed electrode;

a second electrode;

a lower insulating film formed on the second electrode;

a first insulating film which is formed on the lower insulating film between the first electrode and the second electrode and is electretized, an air gap being formed between the first insulating film and the first electrode; [[and]]

a second insulating film formed so as to cover upper, ~~lower~~ and side surfaces of the first insulating film,

~~wherein the first insulating film covered with the second insulating film is formed on the second electrode~~;

the second electrode, the lower insulating film, the first insulating film, and the second insulating film compose a vibrating film, [[and]]

the second insulating film ~~is formed to be in contact with~~ touches at least one of the upper[[,]] ~~and side and lower~~ surfaces of the first insulating film, and

the lower insulating film and the second insulating film are silicon nitride films.

2. (Currently Amended) ~~A method for manufacturing the~~ The electret condenser of Claim 1,

wherein the first insulating film is a silicon dioxide film grown in an atmosphere at a temperature in a range between 500 °C and 800 °C, both inclusive.

3. (Currently Amended) ~~A method for manufacturing the~~ The electret condenser of Claim 1,

wherein the lower insulating film and the second insulating film ~~[[is]]~~ are a silicon nitride film grown in an atmosphere at a temperature in the range between 600 °C and 800 °C, both inclusive

4. (Cancelled)

5. (Previously presented) The electret condenser of Claim 1,
wherein a shape in plan of the first insulating film is smaller than a shape in plan of the vibrating film, and

the first insulating film is arranged at a central part of the vibrating film.

6. (Currently Amended) An electret condenser, comprising:
a first electrode which is fixed electrode;
a second electrode; ~~[[and]]~~
a first insulating film which is formed on the second electrode between the first electrode and the second electrode and is electretized, an air gap being formed between the first insulating film and the first electrode; and
a second insulating film formed on the first insulating film so as to cover upper and side surfaces of the first insulating film,

wherein ~~a lower surface of the first insulating film is covered with the second electrode~~
~~and upper and side surfaces of the first insulating film are covered with a second insulating film,~~

the second electrode, the first insulating film, and the second insulating film compose a vibrating film, [[and]]

the second insulating film is ~~formed to be in contact with~~ touches at least one of the upper and side surfaces of the first insulating film, and

the second insulating film is a silicon nitride film.

7. (Currently Amended) ~~A method for manufacturing the~~ The electret condenser of Claim 6,

wherein the first insulating film is a silicon dioxide film grown in an atmosphere at a temperature in a range between 500 °C and 800 °C, both inclusive.

8. (Currently Amended) ~~A method for manufacturing the~~ The electret condenser of Claim 6,

wherein the second insulating film is ~~a silicon nitride film~~ grown in an atmosphere at a temperature in the range between 600 °C and 800 °C, both inclusive.

9. (Cancelled)

10. (Previously presented) The electret condenser of Claim 6,
wherein a shape in plan of the first insulating film is smaller than a shape in plan of the vibrating film, and

the first insulating film is arranged at a central part of the vibrating film.

11. (Currently Amended) The electret condenser of claim 1,
wherein the second insulating film ~~is formed to be in contact with~~ touches the upper and
side surfaces of the first insulating film.

12-13. (Cancelled)

14. (Currently Amended) The electret condenser of claim 6,
wherein the second insulating film ~~is formed to be in contact with~~ touches the upper and
side surfaces of the first insulating film.

15. (Currently Amended) The electret condenser of claim 6,
wherein the second insulating film ~~is formed to be in contact with~~ touches the upper and
side surfaces of the first insulating film, and
the second electrode ~~is formed to be in contact with~~ touches the lower surface of the first
insulating film.

16. (Cancelled)

17. (Currently Amended) An electret condenser, comprising:
a first electrode;
a second electrode;
a first insulating film which is formed between the first electrode and the second
electrode and is electretized; and

a second insulating film formed so as to ~~be in contact with at least one of~~ touch all of
upper, lower and side surfaces of the first insulating film,

wherein the second insulating film is a silicon nitride film.

18. (Previously presented) The electret condenser of claim 17,
wherein the first insulating film is formed on the second electrode.

19. (Previously presented) The electret condenser of claim 17,
wherein at least one of the first electrode and the second electrode is included in a
vibrating film.

20-22. (Cancelled)

23. (Currently Amended) The electret condenser of claim 17,
wherein the first insulating film is made of [[a]] silicon dioxide [[film]].

24. (Cancelled)